

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A semiconductor device, comprising:
a semiconductor substrate that includes an active element and an integrated circuit having an active element in the active element region;
electrodes electrically connected to the integrated circuit, the electrodes including a first electrode and a second electrode;
a resin layer that is formed on a surface of the semiconductor substrate where the electrode is also formed, so as to avoid at least a part of the electrodes;
a wiring layer that extends from the electrode and across a top of the resin layer, and includes a plurality of electrically connecting portions, the plurality of electrically connecting portions including a first electrically connecting portion electrically connected to the first electrode and a second electrically connecting portion electrically connected to the second electrode, a surface area of the first electrically connecting portion being larger than a surface area of the second electrically connecting portion, the surface area of the first electrically connecting portion being larger than the active element region; and
an external terminal that is provided on the electrically connecting portions.
2. (Original) The semiconductor device according to claim 1, the second electrically connecting portion being formed on the top surface of the resin layer.
3. (Original) The semiconductor device according to claim 1, the resin layer overlapping the active element region of the semiconductor substrate; and
the first electrically connecting portion being formed on the area of the resin layer that overlaps the active element region.

4. (Original) The semiconductor device according to claim 1, the first electrically connecting portion being formed so as to cover nearly the entire top surface of the resin layer.

5. (Original) The semiconductor device according to claim 4, the first electrically connecting portion being formed so as to further cover a side surface of the resin layer.

6. (Original) The semiconductor device according to claim 5, the first electrically connecting portion being formed so as to extend to the region of the substrate beyond the resin layer.

7. (Original) The semiconductor device according to claim 1, the first electrically connecting portion supplying at least one of a ground potential and a power-source potential.

8. (Original) The semiconductor device according to claim 7, the first electrically connecting portion being formed in at least one of a shape and a size that provides predetermined electrical characteristics.

9. (Original) The semiconductor device according to claim 1, further comprising an insulating layer formed so as to cover the wiring layer while avoiding the external terminal.

10. (Original) The semiconductor device according to claim 1, the semiconductor substrate being at least one of a semiconductor chip and a semiconductor wafer.

11. (Currently Amended) A semiconductor device, comprising:
a semiconductor substrate that includes an active element region and an integrated circuit having an active element in the active element region;
electrodes electrically connected to the integrated circuit, the electrodes including a first electrode and a second electrode;

a resin layer that is formed on a surface of the semiconductor substrate where the electrode is also formed, so as to avoid at least a part of the electrodes;

a wiring layer that extends from the electrode and across a top of the resin layer, and includes a plurality of electrically connecting portions, the wiring layer including a first electrically connecting portion electrically connected to the first electrode and a second electrically connecting portion electrically connected to the second electrode, the first electrically connecting portion covering the entire surface of the resin layer except for the area occupied by the wiring layer including the second electrically connecting portion and the area surrounding the wiring layer including the second electrically connecting portion, the surface area of the first electrically connecting portion being larger than the active element region;
and

an external terminal that is provided on the electrically connecting portions.

12. (Original) A circuit board, comprising:

the semiconductor device according to claim 1.

13. (Original) An electronic device, comprising:

the semiconductor device according to claim 1.

14. (Currently Amended) A method of manufacturing a semiconductor device, comprising:

(a) forming a resin layer on a surface of a semiconductor substrate, the semiconductor substrate including an active element region, an integrated circuit having an active element in the active element region, and electrodes electrically connected to the integrated circuit, the electrode including a first electrode and a second electrode, the resin layer being formed so as to avoid at least a part of the electrodes;

(b) forming a wiring layer from the electrode across a top of the resin layer so that the wiring layer include a plurality of electrically connecting portions, the plurality of

electrically connecting portions include a first electrically connecting portion and a second electrically connecting portion;

(c) providing an external terminal on the electrically connecting portions; and wherein the plurality of electrically connecting portions formed in step (b) so that a surface area of a first electrically connecting portion is larger than a surface area of a second electrically connecting portion and the surface area of the first electrically connecting portion being larger than the active element region.